



MMBT3906

PNP GENERAL PURPOSE SWITCHING TRANSISTOR

VOLTAGE 40 Volts **POWER** 225 mWatts **SOT-23** Unit: inch (mm)

FEATURES

- PNP epitaxial silicon, planar design
- Collector-emitter voltage $V_{CE} = -40V$
- Collector current $I_C = -200mA$
- In compliance with EU RoHS 2002/95/EC directives

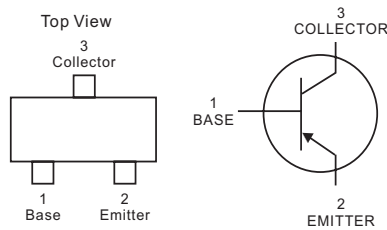
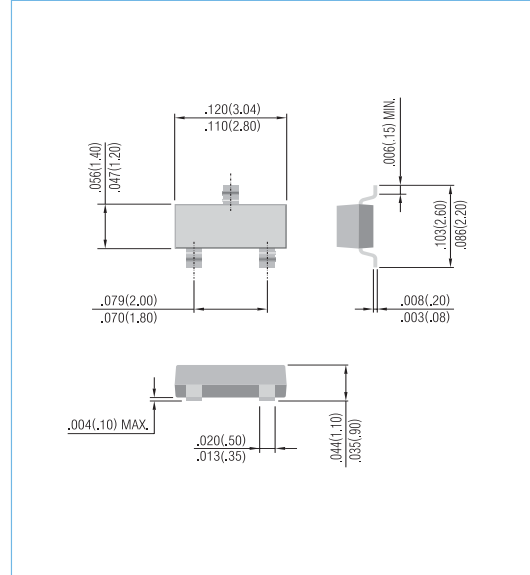
MECHANICAL DATA

Case: SOT-23, Plastic

Terminals: Solderable per MIL-STD-750, Method 2026

Approx. Weight: 0.008 gram

Marking: S2A



ABSOLUTE RATINGS

PARAMETER	Symbol	Value	Units
Collector - Emitter Voltage	V_{CEO}	-40	V
Collector - Base Voltage	V_{CBO}	-40	V
Emitter - Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-200	mA

THERMAL CHARACTERISTICS

PARAMETER	Symbol	Value	Units
Max Power Dissipation (Note 1)	P_{TOT}	225	mW
Thermal Resistance , Junction to Ambient	$R_{\theta JA}$	556	$^{\circ}C/W$
Junction Temperature	T_J	-55 to 150	$^{\circ}C$
Storage Temperature	T_{STG}	-55 to 150	$^{\circ}C$

Note 1: Transistor mounted on FR-5 board 1.0 x 0.75 x 0.062 in.



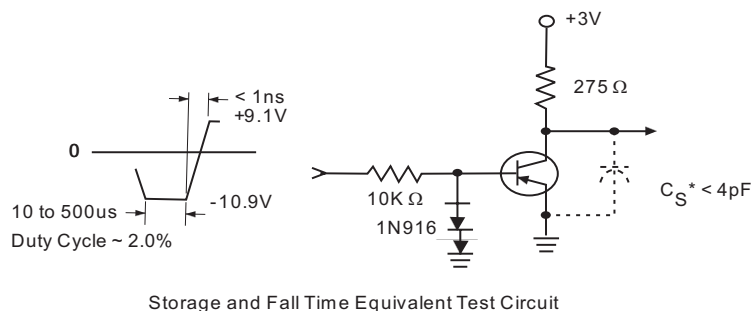
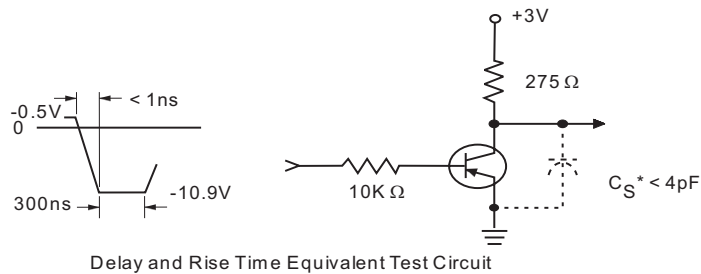
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ELECTRICAL CHARACTERISTICS

PARAMETER	Symbol	Test Condition	MIN.	TYP.	MAX.	Units
Collector - Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -1.0\text{mA}, I_B = 0$	-40	-	-	V
Collector - Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = -10\mu\text{A}, I_E = 0$	-40	-	-	V
Emitter - Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = -10\mu\text{A}, I_C = 0$	-5.0	-	-	V
Base Cutoff Current	I_{BL}	$V_{CE} = -30\text{V}, V_{EB} = -3.0\text{V}$	-	-	-50	nA
Collector Cutoff Current	I_{CEX}	$V_{CE} = -30\text{V}, V_{EB} = -3.0\text{V}$	-	-	-50	nA
DC Current Gain (Note 2)	h_{FE}	$I_C = -0.1\text{mA}, V_{CE} = -1.0\text{V}$ $I_C = -1.0\text{mA}, V_{CE} = -1.0\text{V}$ $I_C = -10\text{mA}, V_{CE} = -1.0\text{V}$ $I_C = -50\text{mA}, V_{CE} = -1.0\text{V}$ $I_C = -100\text{mA}, V_{CE} = -1.0\text{V}$	60 80 100 60 30	- - - - -	- - 300 - -	-
Collector - Emitter Saturation Voltage (Note 2)	$V_{CE(SAT)}$	$I_C = -10\text{mA}, I_B = -1.0\text{mA}$ $I_C = -50\text{mA}, I_B = -5.0\text{mA}$	-	-	-0.25 -0.4	V
Base - Emitter Saturation Voltage (Note 2)	$V_{BE(SAT)}$	$I_C = -10\text{mA}, I_B = -1.0\text{mA}$ $I_C = -50\text{mA}, I_B = -5.0\text{mA}$	-0.65 -	- -	-0.85 -0.95	V
Collector - Base Capacitance	C_{CBO}	$V_{CB} = -5\text{V}, I_E = 0, f = 1\text{MHz}$	-	-	4.5	pF
Emitter - Base Capacitance	C_{EBO}	$V_{EB} = -0.5\text{V}, I_C = 0, f = 1\text{MHz}$	-	-	10	pF
Delay Time	t_d	$V_{CC} = -3\text{V}, V_{BE} = -0.5\text{V}, I_C = -10\text{mA}, I_B = -1.0\text{mA}$	-	-	35	ns
Rise Time	t_r	$V_{CC} = -3\text{V}, V_{BE} = -0.5\text{V}, I_C = -10\text{mA}, I_B = -1.0\text{mA}$	-	-	35	ns
Storage Time	t_s	$V_{CC} = -3\text{V}, I_C = -10\text{mA}, I_{B1} = I_{B2} = -1.0\text{mA}$	-	-	225	ns
Fall Time	t_f	$V_{CC} = -3\text{V}, I_C = -10\text{mA}, I_{B1} = I_{B2} = -1.0\text{mA}$	-	-	75	ns

Note 2: Pulse Test: Pulse Width < 300 us, Duty Cycle < 2.0%.

SWITCHING TIME EQUIVALENT TEST CIRCUITS





ELECTRICAL CHARACTERISTICS CURVE

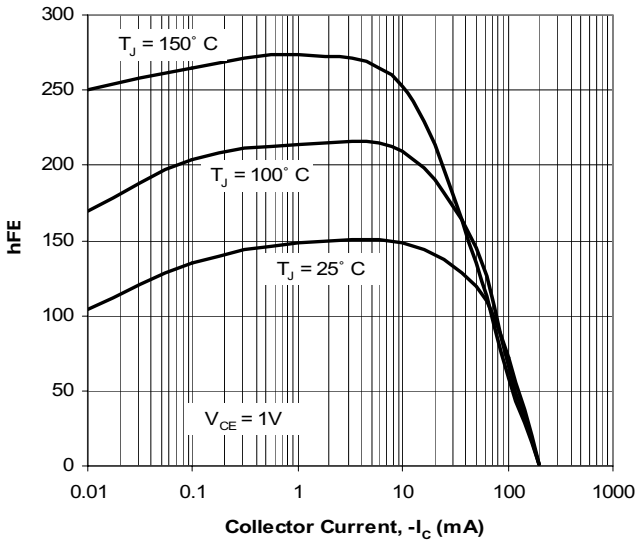


Fig. 1. Typical h_{FE} vs. Collector Current

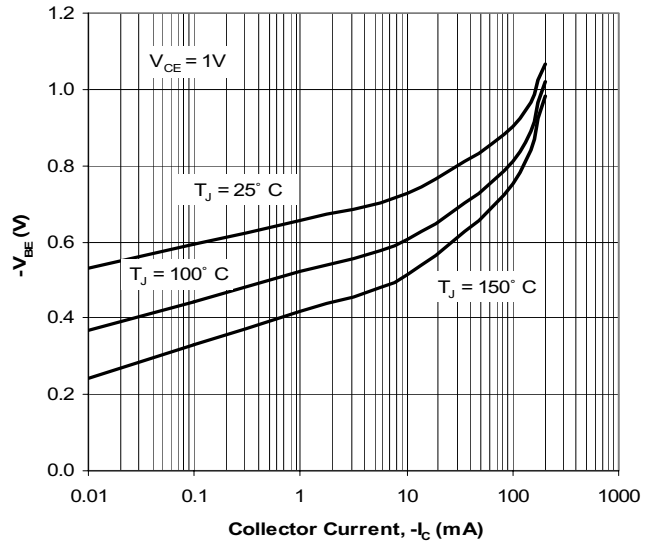


Fig. 2. Typical V_{BE} vs. Collector Current

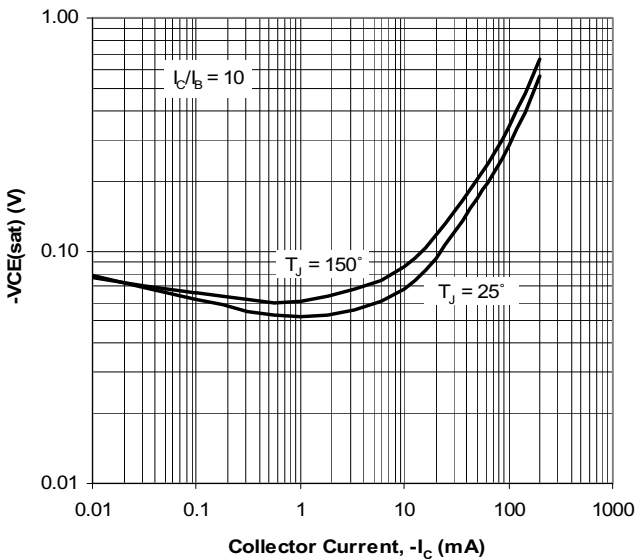


Fig. 3. Typical $V_{CE(sat)}$ vs. Collector Current

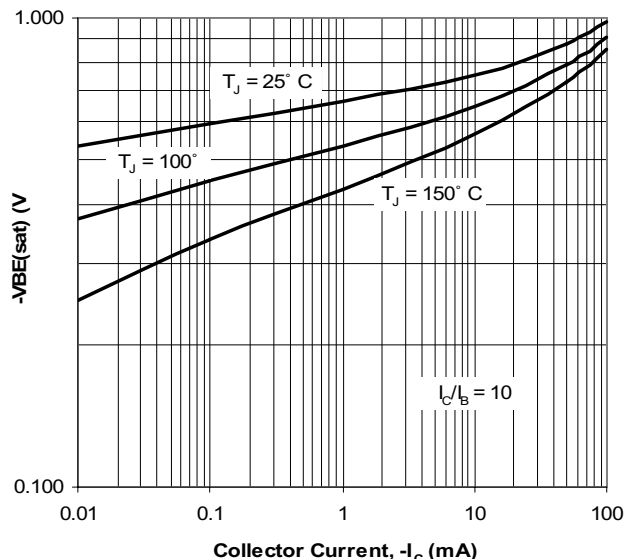


Fig. 4. Typical $V_{BE(sat)}$ vs. Collector Current

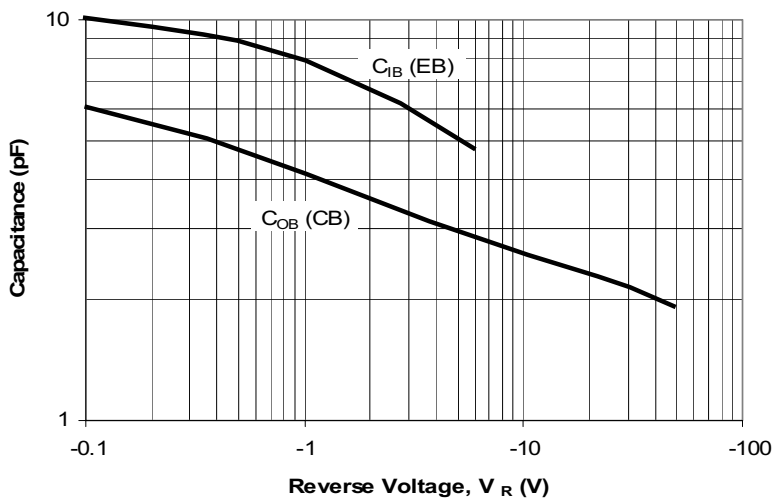
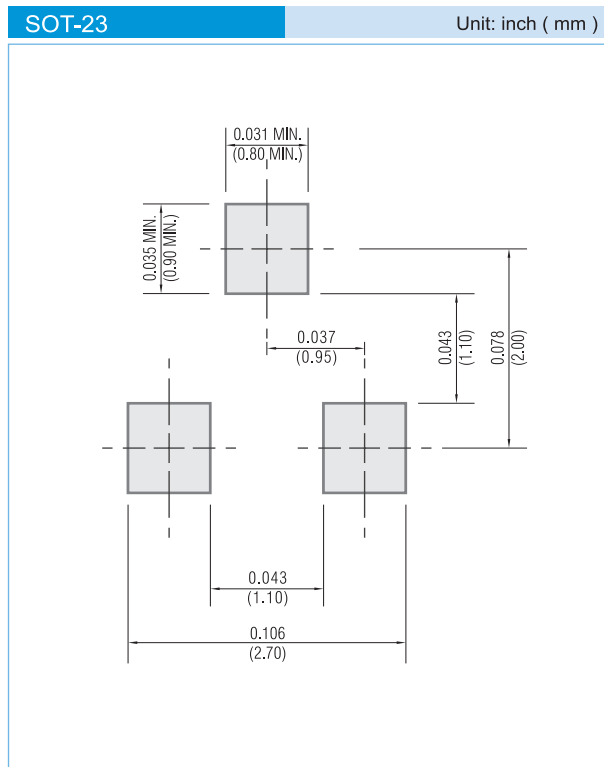


Fig. 5. Typical Capacitances vs. Reverse Voltage



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MOUNTING PAD LAYOUT



ORDER INFORMATION

- Packing information
 - T/R - 12K per 13" plastic Reel
 - T/R - 3K per 7" plastic Reel

LEGAL STATEMENT

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